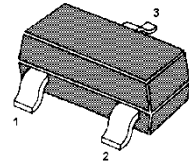


BC846...BC850

NPN Silicon Epitaxial Transistor

for switching and amplifier applications

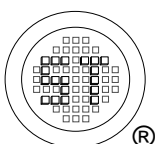
As complementary types the PNP transistors BC856...BC860 is recommended.



1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit | |
|---------------------------|---------------------|---------------|------------------|---|
| Collector Base Voltage | BC846 | V_{CBO} | 80 | V |
| | BC847, BC850 | V_{CBO} | 50 | V |
| | BC848, BC849 | V_{CBO} | 30 | V |
| Collector Emitter Voltage | BC846 | V_{CEO} | 65 | V |
| | BC847, BC850 | V_{CEO} | 45 | V |
| | BC848, BC849 | V_{CEO} | 30 | V |
| Emitter Base Voltage | BC846, BC847 | V_{EBO} | 6 | V |
| | BC848, BC849, BC850 | V_{EBO} | 5 | V |
| Collector Current | I_C | 100 | mA | |
| Peak Collector Current | I_{CM} | 200 | mA | |
| Power Dissipation | P_{tot} | 300 | mW | |
| Junction Temperature | T_j | 150 | $^\circ\text{C}$ | |
| Storage Temperature Range | T_{stg} | - 65 to + 150 | $^\circ\text{C}$ | |



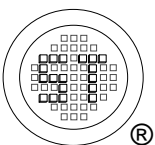
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BC846...BC850

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

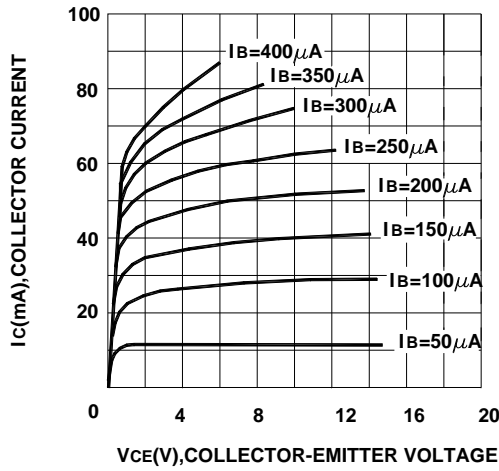
| Parameter | Symbol | Min. | Typ. | Max. | Unit | |
|---|----------------------|---------------|------|------|------|---|
| DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$ | Current Gain Group A | | | | | |
| | h_{FE} | 110 | - | 220 | - | |
| | B | h_{FE} | 200 | - | 450 | - |
| | C | h_{FE} | 420 | - | 800 | - |
| Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$ | I_{CBO} | - | - | 15 | nA | |
| Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$ | BC846 | $V_{(BR)CBO}$ | 80 | - | - | V |
| | BC847, BC850 | $V_{(BR)CBO}$ | 50 | - | - | V |
| | BC848, BC849 | $V_{(BR)CBO}$ | 30 | - | - | V |
| Collector Emitter Breakdown Voltage at $I_C = 2\text{ mA}$ | BC846 | $V_{(BR)CEO}$ | 65 | - | - | V |
| | BC847, BC850 | $V_{(BR)CEO}$ | 45 | - | - | V |
| | BC848, BC849 | $V_{(BR)CEO}$ | 30 | - | - | V |
| Collector Emitter Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$ | BC846, BC847 | $V_{(BR)EBO}$ | 6 | - | - | V |
| | BC848, BC849, BC850 | $V_{(BR)EBO}$ | 5 | - | - | V |
| Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ at $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$ | V_{CEsat} | - | - | 250 | mV | |
| | V_{CEsat} | - | - | 600 | mV | |
| Base Emitter On Voltage at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$ | $V_{BE(on)}$ | 580 | - | 700 | mV | |
| | $V_{BE(on)}$ | - | - | 720 | mV | |
| Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$ | f_T | - | 300 | - | MHz | |
| Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$ | C_{ob} | - | - | 6 | pF | |
| Input Capacitance at $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$ | C_{ib} | - | 9 | - | pF | |



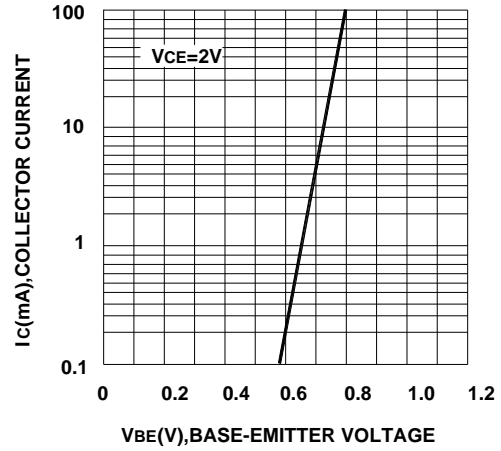
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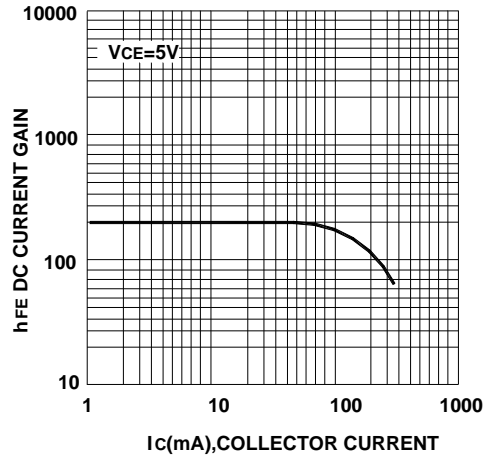
STATIC CHARACTERISTIC



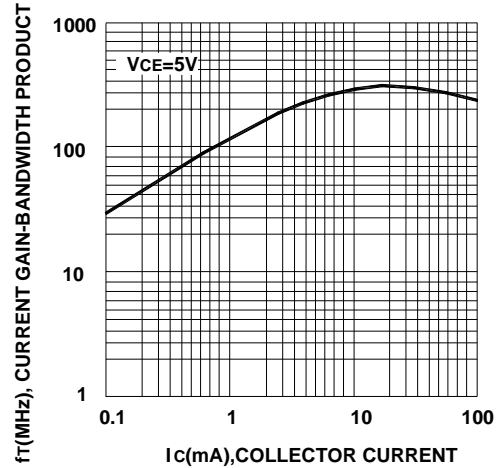
BASE-EMITTER ON VOLTAGE



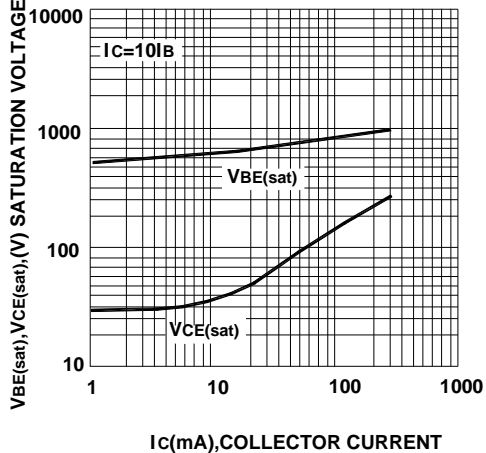
DC CURRENT GAIN



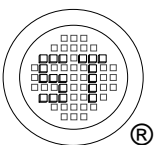
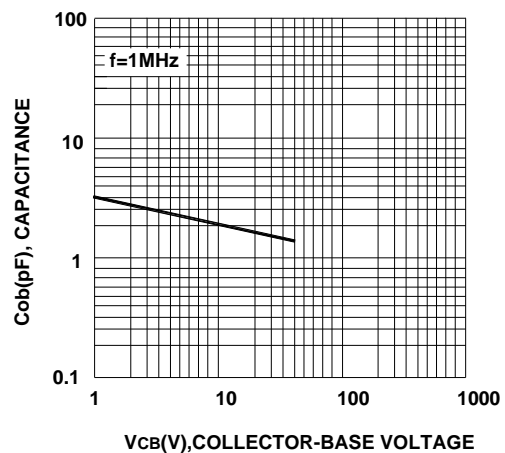
CURRENT GAIN BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



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ISO/TS 16949:2009
Certificate No. 180713000

ISO14001:2004
Certificate No. 7116

ISO 9001:2008
Certificate No. 50719410

BS-OHSAS 18001:2007
Certificate No. 7116

IECQ QC 080000
Certificate No. PRC-HSPM-1485-1